NEC

BIPOLAR ANALOG INTEGRATED CIRCUIT

μPC8230TU

SiGe:C LOW NOISE AMPLIFIER FOR GPS

DESCRIPTION

The μPC8230TU is a silicon germanium carbon (SiGe:C) monolithic integrated circuit designed as low noise amplifier for GPS. This device exhibits low noise figure and high power gain characteristics, so this IC can improve the sensitivity of GPS receiver. In addition, the μPC8230TU which is included output matching circuit contributes to reduce external components and system size.

The package is 8-pin lead-less minimold suitable for surface mount.

This IC is manufactured using our UHS4 (Ultra High Speed Process) SiGe:C bipolar process.

FEATURES

- Low noise : NF = 0.85 dB TYP. @ f_{in} = 1 575 MHz
- High gain : G_P = 18.5 dB TYP. @ f_{in} = 1 575 MHz
- Low current consumption : I_{CC} = 6.0 mA TYP. @ V_{CC} = 3.0 V
- Built-in power-saving function
- High-density surface mounting : 8-pin lead-less minimold package (2.0 × 2.0 × 0.5 mm)
- Included output matching circuit
- Included very robust bandgap regulator (Small V_{CC} and T_A dependence)
- Included protection circuits for ESD

APPLICATION

- Low noise amplifier for GPS

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC8230TU-E2	μPC8230TU-E2-A	8-pin lead-less minimold (Pb-Free)	8230	• 8 mm wide embossed taping • Pin 5, 6, 7, 8 indicates pull-out direction of tape • Qty 5 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.
Part number for sample order: μPC8230TU

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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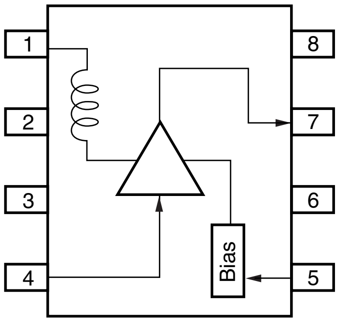
PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM

(Top View)



Pin No.	Pin Name
1	V_{CC}
2	N.C.
3	GND
4	INPUT
5	Power Save
6	GND
7	OUTPUT
8	V_{CC}

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Ratings	Unit
Supply Voltage	V_{CC}	T_A = +25°C	4.0	V
Power-Saving Voltage	V_{PS}	T_A = +25°C	4.0	V
Power Dissipation	P_D	T_A = +85°C **Note**	295	mW
Operating Ambient Temperature	T_A		–40 to +85	°C
Storage Temperature	T_{stg}		–55 to +150	°C
Input Power	P_{in}		+10	dBm

Note Mounted on double-side copper-clad 50 × 50 × 1.6 mm epoxy glass PWB

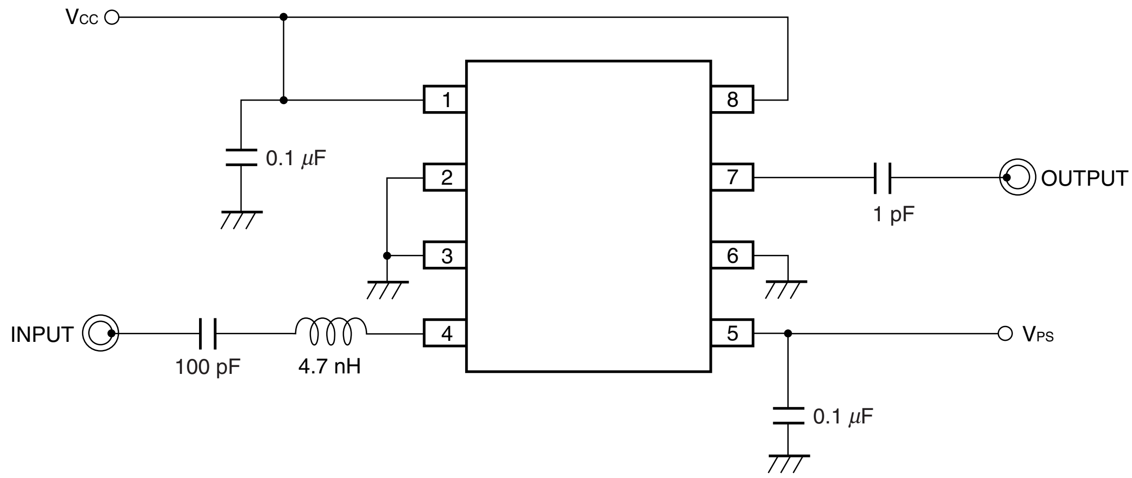
RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}	2.7	3.0	3.3	V
Operating Ambient Temperature	T_A	–40	+25	+85	°C
Power Save Turn-on Voltage	V_{PSon}	2.2	–	V_{CC}	V
Power Save Turn-off Voltage	V_{PSoff}	0	–	0.8	V

ELECTRICAL CHARACTERISTICS
(T_A = +25°C, V_{CC} = V_{PS} = 3.0 V, f_{in} = 1 575 MHz, unless otherwise specified)

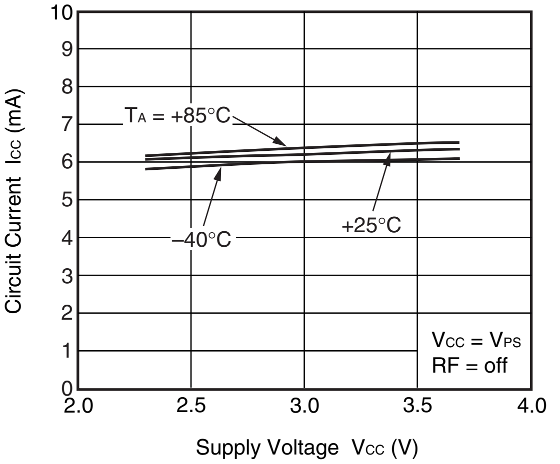
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	I_{CC}	No Signal (V_{PS} = 3.0 V)	4.5	6.0	8.0	mA
		At Power-Saving Mode (V_{PS} = 0 V)	–	–	1	μA
Power Gain	G_P	P_{in} = –35 dBm	16	18.5	21	dB
Noise Figure	NF		–	0.85	1.15	dB
Input 3rd Order Distortion Intercept Point	IIP_3	$f_{in}1$ = 1 574 MHz, $f_{in}2$ = 1 575 MHz	–	–5	–	dBm
Input Return Loss	RL_{in}		8	11	–	dB
Output Return Loss	RL_{out}		7	10	–	dB
Isolation	ISL		–	39	–	dB
Gain 1 dB Compression Input Power	$P_{in\ (1\ dB)}$		–	–17	–	dBm

TEST CIRCUIT

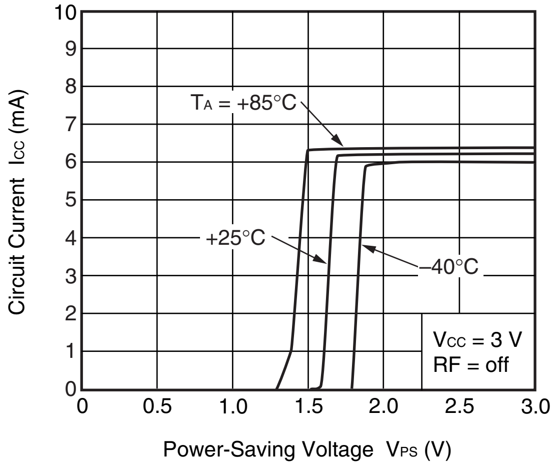


TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

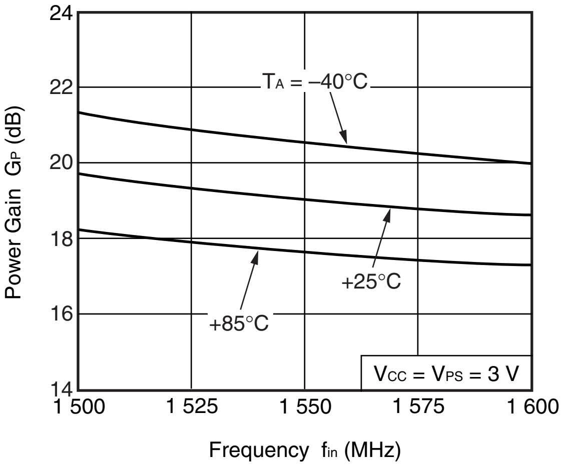
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



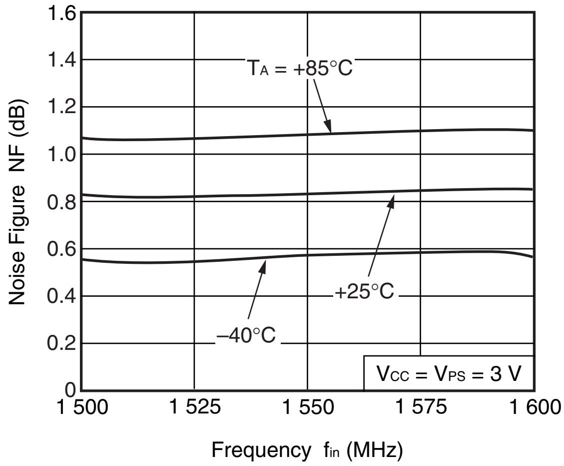
CIRCUIT CURRENT vs.
POWER-SAVING VOLTAGE



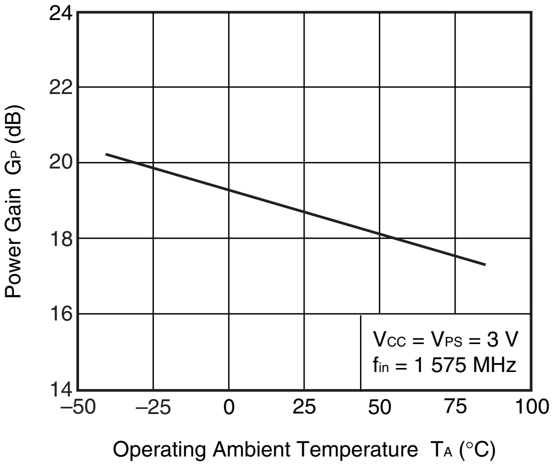
POWER GAIN vs. FREQUENCY



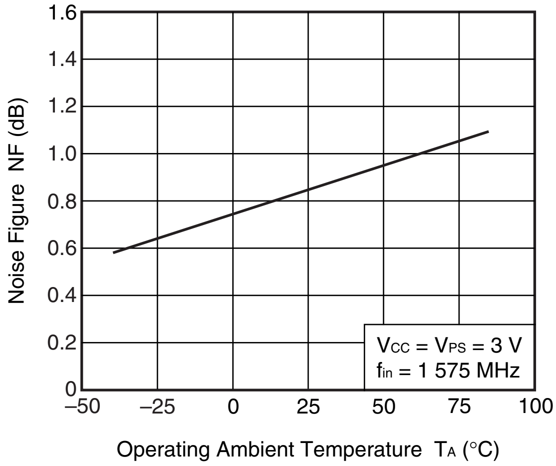
NOISE FIGURE vs. FREQUENCY



POWER GAIN vs. OPERATING
AMBIENT TEMPERATURE

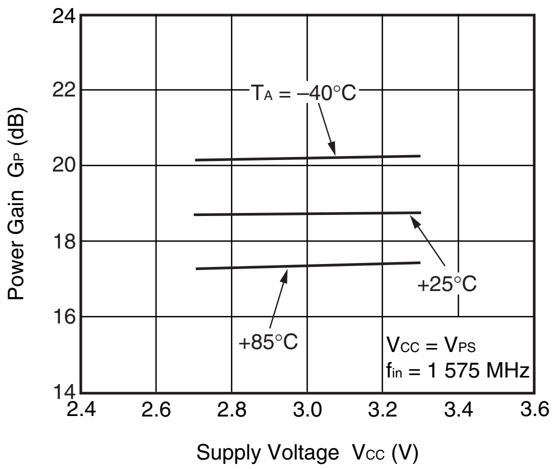


NOISE FIGURE vs. OPERATING
AMBIENT TEMPERATURE

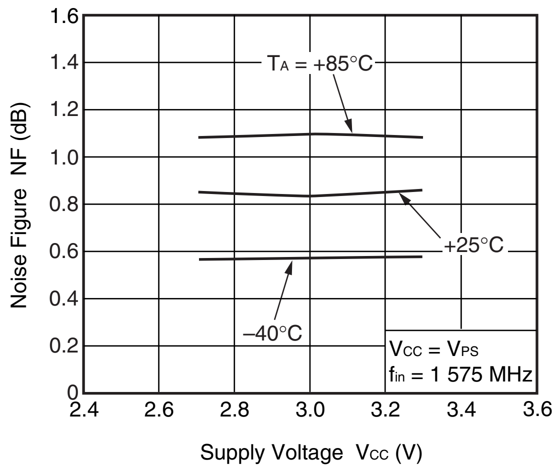


Remark The graphs indicate nominal characteristics.

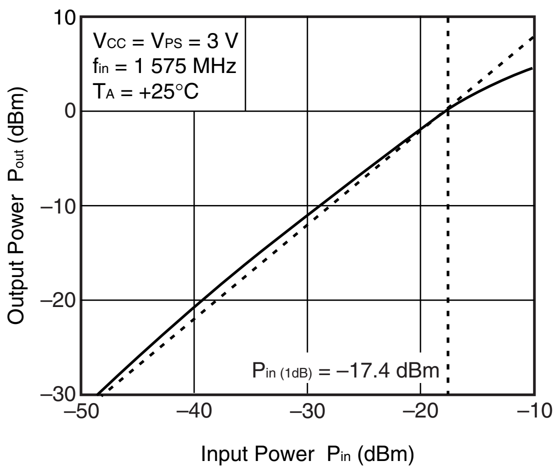
POWER GAIN vs. SUPPLY VOLTAGE



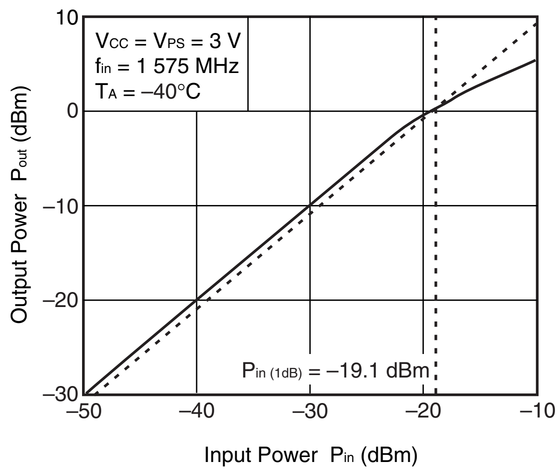
NOISE FIGURE vs. SUPPLY VOLTAGE



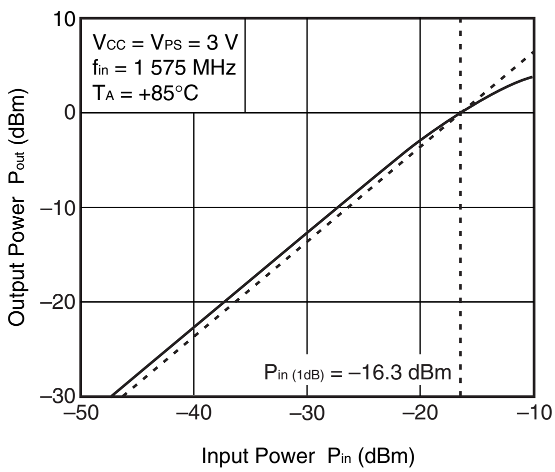
OUTPUT POWER vs. INPUT POWER



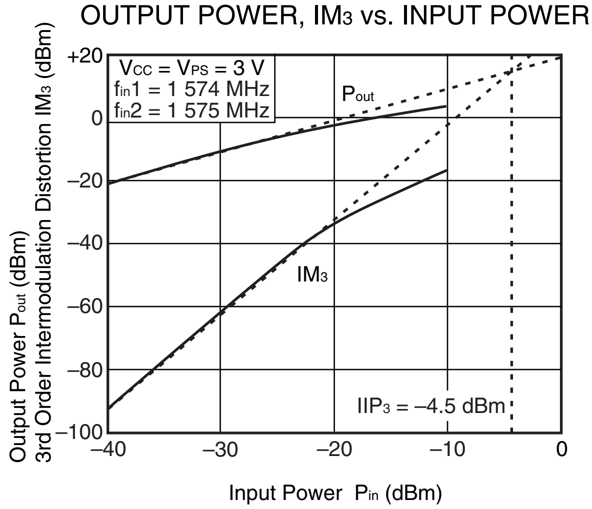
OUTPUT POWER vs. INPUT POWER



OUTPUT POWER vs. INPUT POWER



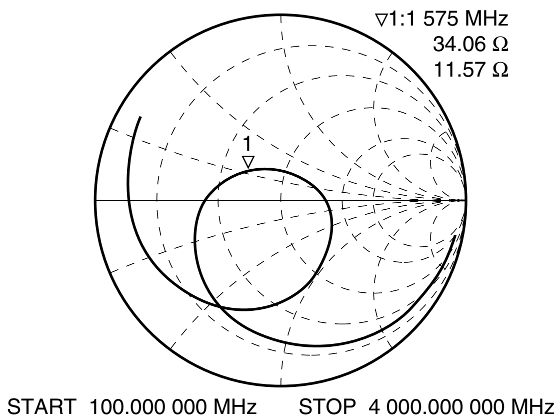
OUTPUT POWER, IM3 vs. INPUT POWER



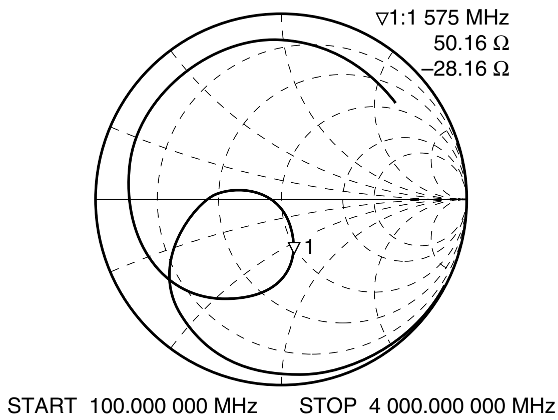
Remark The graphs indicate nominal characteristics.

S-PARAMETERS (T_A = +25°C, V_{CC} = V_{PS} = 3.0 V, monitored at connector on board)

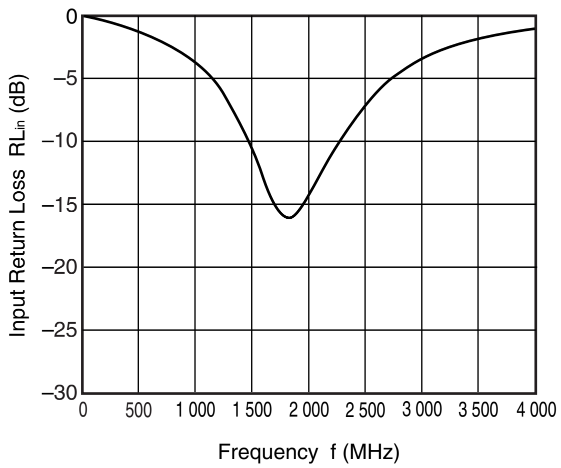
S_{11}–FREQUENCY



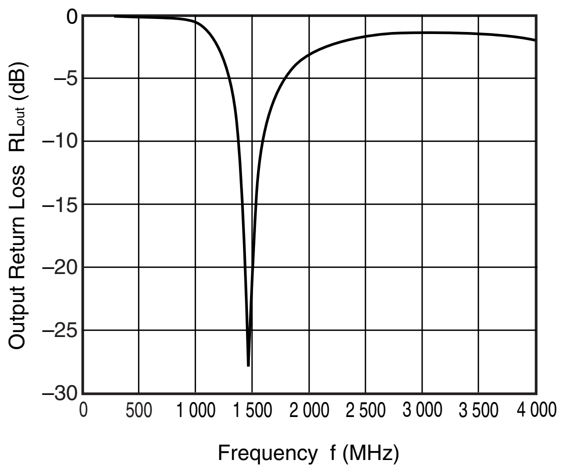
S_{22}–FREQUENCY



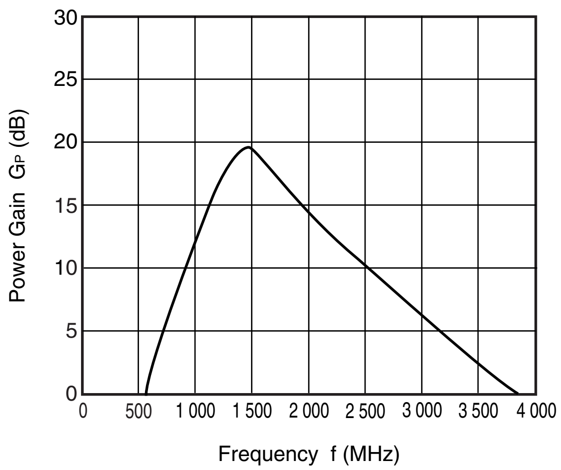
INPUT RETURN LOSS vs. FREQUENCY



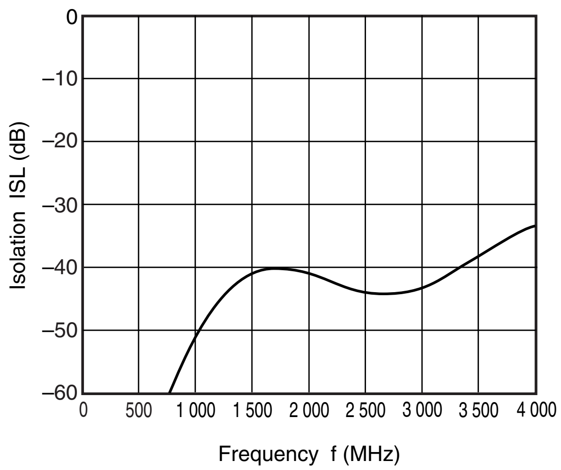
OUTPUT RETURN LOSS vs. FREQUENCY



POWER GAIN vs. FREQUENCY



ISOLATION vs. FREQUENCY

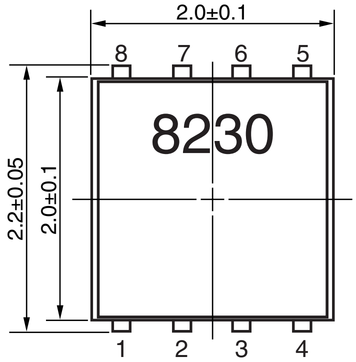


Remark The graphs indicate nominal characteristics.

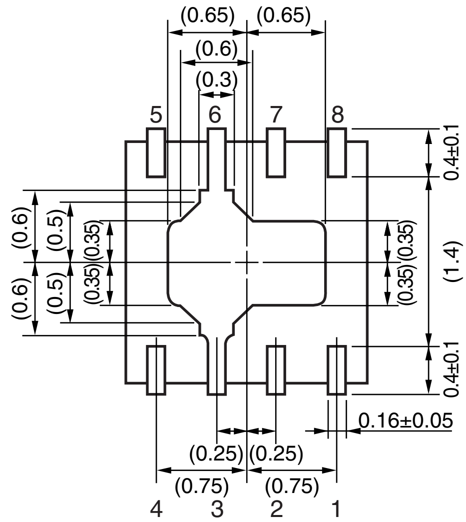
PACKAGE DIMENSIONS

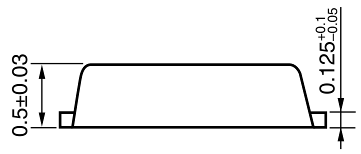
8-PIN LEAD-LESS MINIMOLD (UNIT: mm)

(Top View)



(Bottom View)





Remark ( ) : Reference value

NOTES ON CORRECT USE

(1) Observe precautions for handling because of electro-static sensitive devices.
(2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.
(3) The bypass capacitor should be attached to V_{CC} line.
(4) Do not supply DC voltage to INPUT pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

▶**For further information, please contact**

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